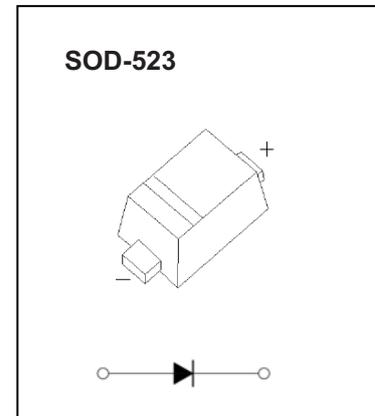


## BAT30WT SCHOTTKY BARRIER DIODE

### FEATURES

- Low capacitance diode
- Very low conduction losses
- Low forward and reverse recovery times

**MARKING: 30**



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Forward Current	$I_F$	300	mA
Repetitive Peak Forward Current $T_a = 85^\circ\text{C}$ , $\delta = 0.1$	$I_{FRM}$	0.9	A
Peak Forward Surge Current ( $t_p = 10\text{ ms}$ )	$I_{FSM}$	1	A
Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Typical Thermal Resistance Junction to Ambient <sup>1)</sup>	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$

<sup>1)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

**Characteristics at  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	30	-	-	V
Forward Voltage at $I_F = 0.1 \text{ mA}$ at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 30 \text{ mA}$ at $I_F = 100 \text{ mA}$ at $I_F = 200 \text{ mA}$	$V_F$	- - - - - -	- - - - - -	240 300 375 430 500 580	mV
Reverse Current at $V_R = 5 \text{ V}$ at $V_R = 10 \text{ V}$ at $V_R = 25 \text{ V}$ at $V_R = 30 \text{ V}$ at $V_R = 10 \text{ V}$ , $T_j = 85^\circ\text{C}$	$I_R$	- - - - -	- - - - 18	0.5 1 3 5 -	$\mu\text{A}$
Total Capacitance at $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ at $V_R = 1 \text{ V}$ , $f = 1 \text{ MHz}$ at $V_R = 10 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	- - -	22 14 6	- - -	pF

## Typical Characteristics

Fig 1. Reverse Characteristic Curve

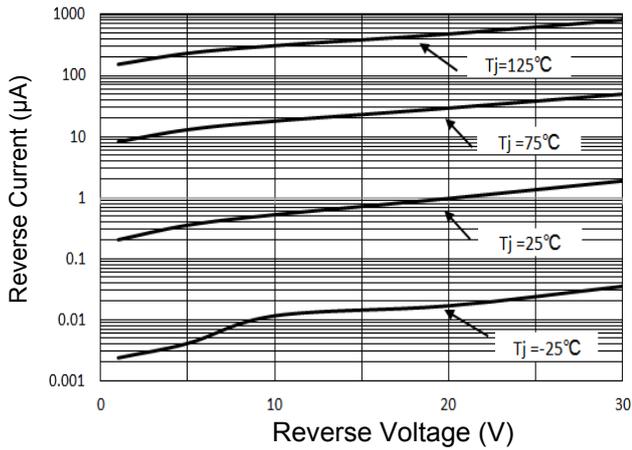


Fig 2. Forward Characteristic Curve

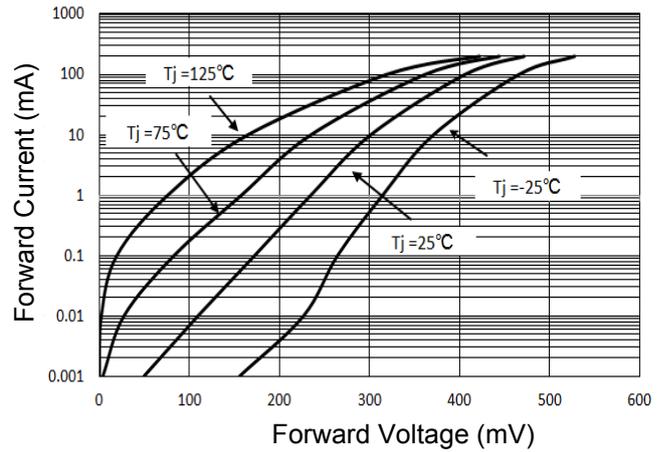


Fig 3. Junction Capacitance

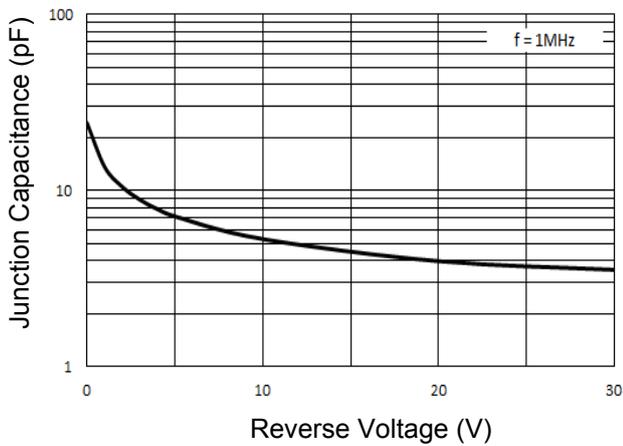


Fig 4. Forward Current Derating Curve

